

PMDPB70XPE 20 V dual P-channel Trench MOSFET Rev. 1 — 20 June 2012

Product data sheet

Product profile 1.

1.1 General description

Dual small-signal P-channel enhancement mode Field-Effect Transistor (FET) in a leadless medium power DFN2020-6 (SOT1118) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

1.2 Features and benefits

- Very fast switching
- Trench MOSFET technology

1.3 Applications

- Relay driver
- High-speed line driver

- 2 kV ElectroStatic Discharge (ESD) protection
- High-side load switch
- Switching circuits

1.4 Quick reference data

Table 1.	Quick reference data						
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per trans	istor						
V _{DS}	drain-source voltage	T _j = 25 °C		-	-	-20	V
V _{GS}	gate-source voltage			-12	-	12	V
I _D	drain current	V_{GS} = -4.5 V; T_{amb} = 25 °C; t ≤ 5 s	<u>[1]</u>	-	-	-4.2	А
Static cha	aracteristics (per transistor)						
R_{DSon}	drain-source on-state resistance	V_{GS} = -4.5 V; I _D = -2 A; T _j = 25 °C		-	66	79	mΩ

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm².



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2. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S1	source TR1		54 50
2	G1	gate TR1	6 5 4	
3	D2	drain TR2		
4	S2	source TR2	7 8	$G_1 \left(\begin{array}{c} \\ \\ \\ \\ \\ \\ \\ \\ \end{array} \right) \left(\begin{array}{c} \\ \\ \\ \\ \\ \end{array} \right) \left(\begin{array}{c} \\ \\ \\ \\ \\ \end{array} \right) \left(\begin{array}{c} \\ \\ \\ \\ \\ \end{array} \right) \left(\begin{array}{c} \\ \\ \\ \\ \\ \end{array} \right) \left(\begin{array}{c} \\ \\ \\ \\ \\ \end{array} \right) \left(\begin{array}{c} \\ \\ \\ \\ \\ \end{array} \right) \left(\begin{array}{c} \\ \\ \\ \\ \\ \end{array} \right) \left(\begin{array}{c} \\ \\ \\ \\ \\ \end{array} \right) \left(\begin{array}{c} \\ \\ \\ \\ \\ \end{array} \right) \left(\begin{array}{c} \\ \\ \\ \\ \\ \\ \end{array} \right) \left(\begin{array}{c} \\ \\ \\ \\ \\ \\ \end{array} \right) \left(\begin{array}{c} \\ \\ \\ \\ \\ \\ \end{array} \right) \left(\begin{array}{c} \\ \\ \\ \\ \\ \\ \\ \end{array} \right) \left(\begin{array}{c} \\ \\ \\ \\ \\ \\ \\ \\ \end{array} \right) \left(\begin{array}{c} \\ \\ \\ \\ \\ \\ \\ \\ \\ \end{array} \right) \left(\begin{array}{c} \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \end{array} \right) \left(\begin{array}{c} \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\$
5	G2	gate TR2		
6	D1	drain TR1	1 2 3	
7	D1	drain TR1	Transparent top view	S1 S2 017aaa260
8	D2	drain TR2	DFN2020-6 (SOT1118)	

3. Ordering information

Table 3. Ordering information					
Type number	Package				
	Name	Description	Version		
PMDPB70XPE	DFN2020-6	plastic thermal enhanced ultra thin small outline package; no leads; 6 terminals	SOT1118		

4. Marking

Table 4. Marking codes	
Type number	Marking code
PMDPB70XPE	2B

5. Limiting values

Table 5.Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
Per transist	tor					
V _{DS}	drain-source voltage	T _j = 25 °C		-	-20	V
V _{GS}	gate-source voltage			-12	12	V
I _D drain current	drain current	$V_{GS} = -4.5 \text{ V}; \text{ T}_{amb} = 25 \text{ °C}; \text{ t} \le 5 \text{ s}$	[1]	-	-4.2	А
		$V_{GS} = -4.5 \text{ V}; \text{ T}_{amb} = 25 \text{ °C}$	[1]	-	-3	А
		$V_{GS} = -4.5 \text{ V}; \text{ T}_{amb} = 100 \text{ °C}$	[1]	-	-2.1	А
I _{DM}	peak drain current	$T_{amb} = 25 \text{ °C}; \text{ single pulse}; t_p \le 10 \ \mu s$		-	-12	А
P _{tot}	total power dissipation	$T_{amb} = 25 \ ^{\circ}C$	[2]	-	515	mW
			[1]	-	1210	mW
		T _{sp} = 25 °C		-	8330	mW
Source-dra	in diode					
I _S	source current	T _{amb} = 25 °C	[1]	-	-1.3	А
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Table 5. Limiting values ...continued

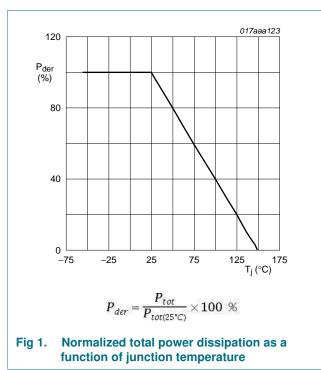
In accordance with the Absolute Maximum Rating System (IEC 60134).

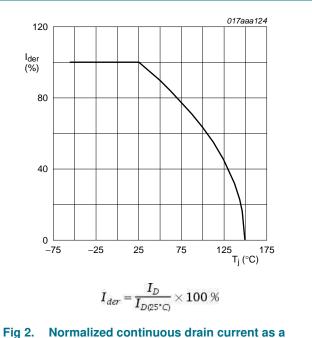
Symbol	Parameter	Conditions		Min	Мах	Unit
ESD maxim	num rating					
V _{ESD}	electrostatic discharge voltage	HBM; C = 100 pF; R = 1.5 k Ω	[3]	-	2000	V
Per device						
Tj	junction temperature			-55	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm².

[2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

[3] Measured between all pins.

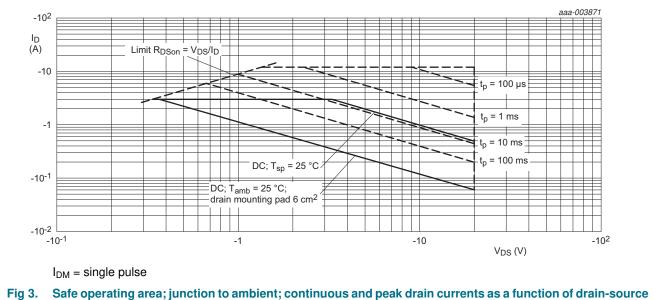






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6. Thermal characteristics

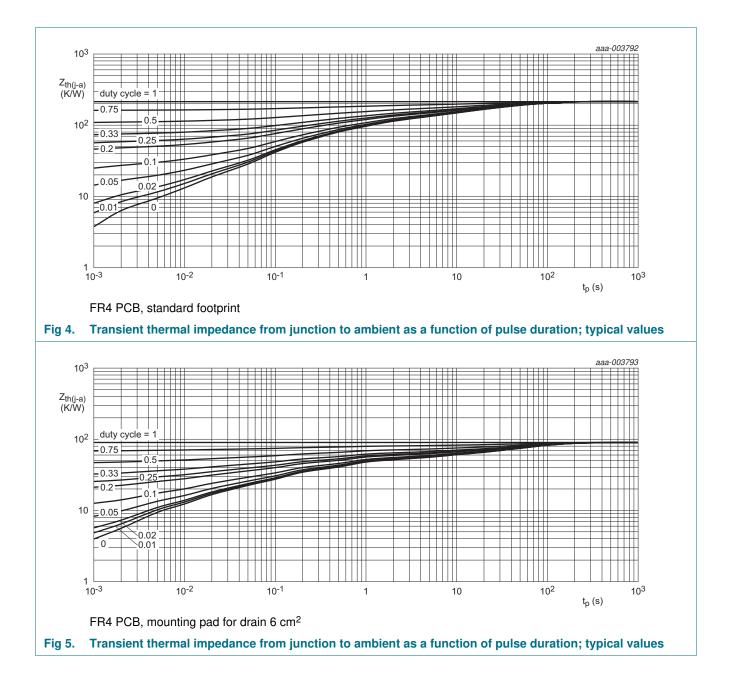
Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transistor	r						
R _{th(j-a)}	thermal resistance	in free air	<u>[1]</u>	-	212	244	K/W
	from junction to ambient		[2]	-	90	104	K/W
		in free air; t ≤ 5 s	[2]	-	55	64	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			-	11	15	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm².

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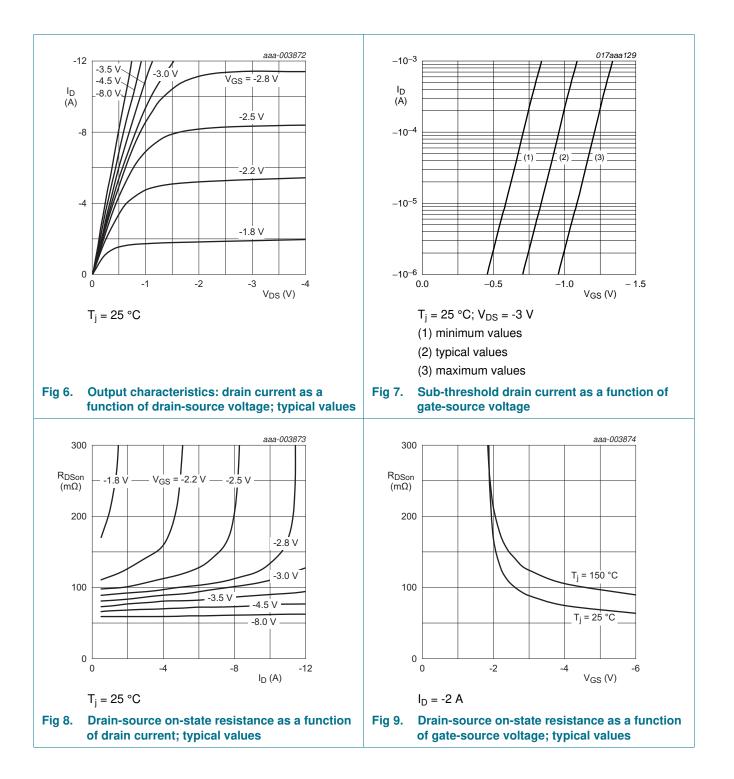


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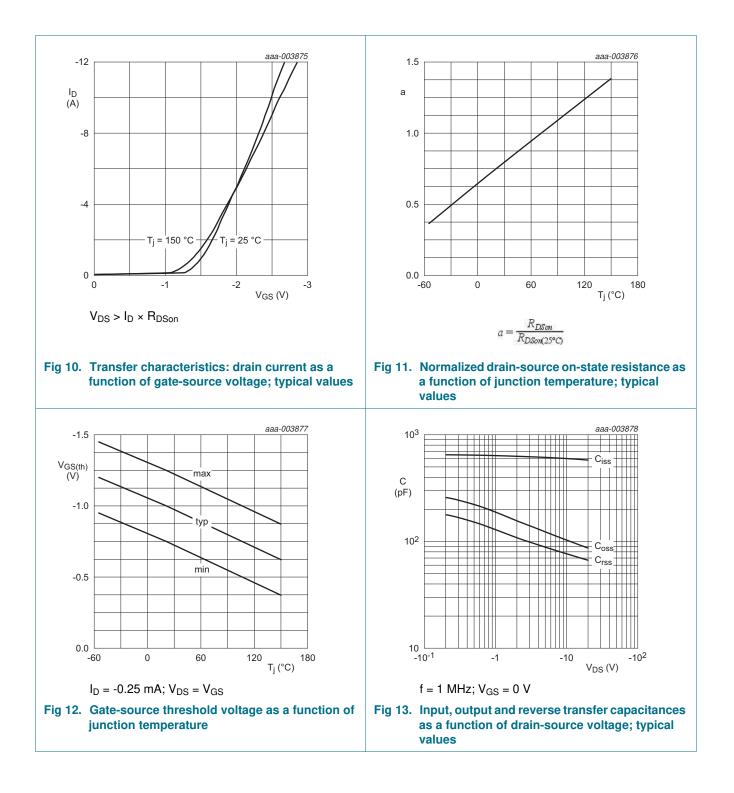
7. Characteristics

Table 7.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	racteristics (per transistor)					
V _{(BR)DSS}	drain-source breakdown voltage	$I_D = -250 \ \mu A; V_{GS} = 0 \ V; T_j = 25 \ ^{\circ}C$	-20	-	-	V
V _{GSth}	gate-source threshold voltage	I_D = -250 µA; V_{DS} = V_{GS} ; T_j = 25 °C	-0.75	-1	-1.25	V
I _{DSS}	drain leakage current	$V_{DS} = -20 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	-1	μA
		$V_{DS} = -20 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 150 \text{ °C}$	-	-	-10	μA
I _{GSS}	gate leakage current	V_{GS} = 12 V; V_{DS} = 0 V; T_j = 25 °C	-	-	10	μA
		$V_{GS} = -12 \text{ V}; \text{ V}_{DS} = 0 \text{ V}; \text{ T}_{j} = 25 \text{ °C}$	-	-	-10	μA
R _{DSon}		V_{GS} = -4.5 V; I _D = -2 A; T _j = 25 °C	-	66	79	mΩ
	resistance	$V_{GS} = -4.5 \text{ V}; I_D = -2 \text{ A}; T_j = 150 \text{ °C}$	-	94	112	mΩ
		V _{GS} = -2.5 V; I _D = -1.5 A; T _j = 25 °C	-	98	123	mΩ
9 _{fs}	forward transconductance	V_{DS} = -10 V; I_D = -2 A; T_j = 25 °C	-	7.3	-	S
Dynamic	characteristics (per transist	or)				
Q _{G(tot)}	total gate charge	V_{DS} = -10 V; I_{D} = -2 A; V_{GS} = -4.5 V;	-	5	7.5	nC
Q _{GS}	gate-source charge	T _j = 25 °C	-	1.1	-	nC
Q _{GD}	gate-drain charge		-	1.1	-	nC
C _{iss}	input capacitance	$V_{DS} = -10 \text{ V}; \text{ f} = 1 \text{ MHz}; \text{ V}_{GS} = 0 \text{ V};$	-	600	-	pF
C _{oss}	output capacitance	T _j = 25 °C	-	103	-	pF
C _{rss}	reverse transfer capacitance		-	77	-	pF
t _{d(on)}	turn-on delay time	V_{DS} = -10 V; I_{D} = -2 A; V_{GS} = -4.5 V;	-	7	-	ns
t _r	rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 °C$	-	16	-	ns
t _{d(off)}	turn-off delay time		-	33	-	ns
t _f	fall time		-	15	-	ns
Source-d	rain diode (per transistor)					
V _{SD}	source-drain voltage	I _S = -0.5 A; V _{GS} = 0 V; T _i = 25 °C	-	-0.7	-1.2	V

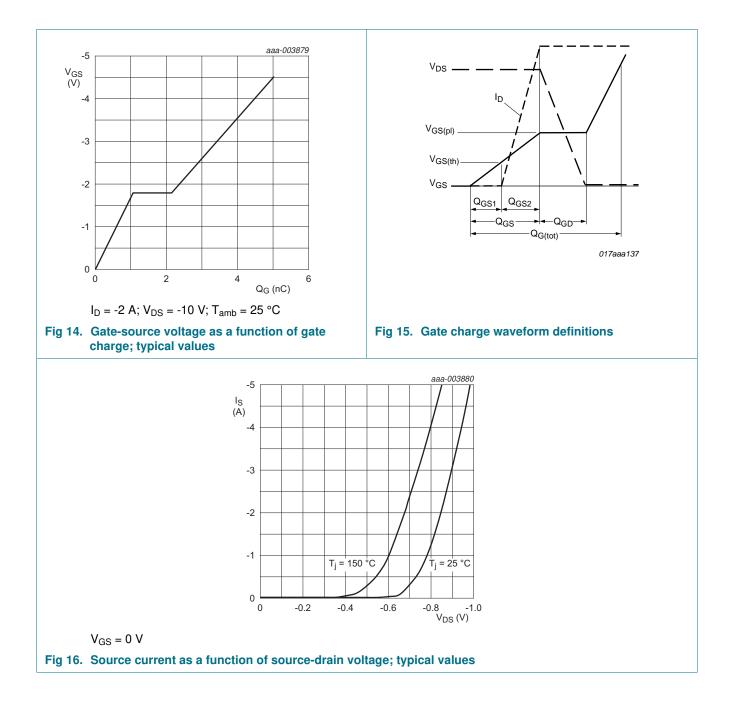
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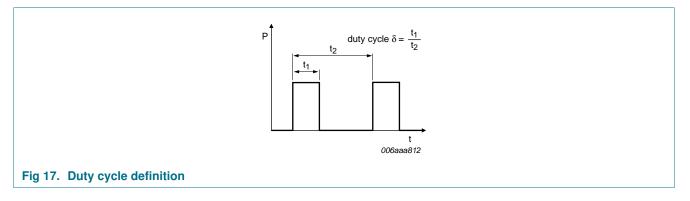


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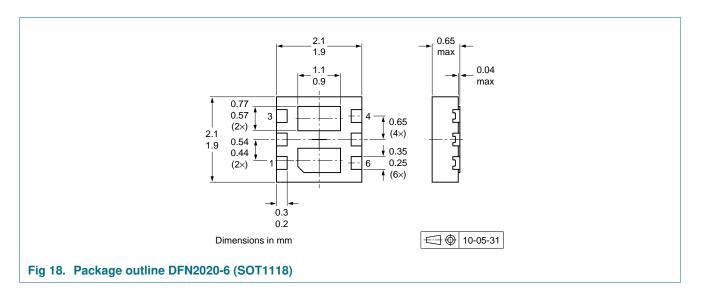


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8. Test information

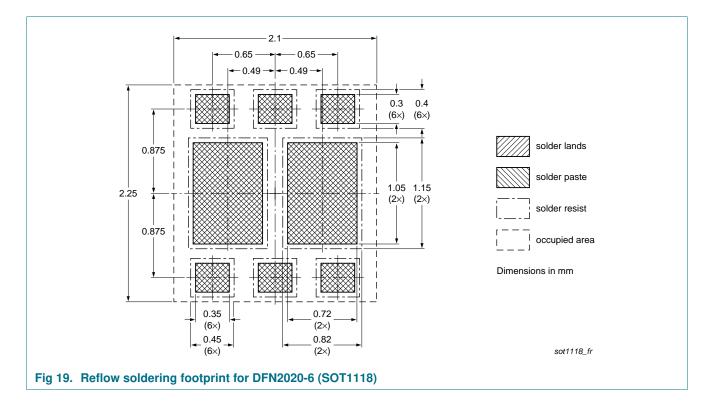


9. Package outline



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10. Soldering



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11. Revision history

Table 8. Re	Revision history					
Document ID)	Release date	Data sheet status	Change notice	Supersedes	
PMDPB70XP	E v.1	20120620	Product data sheet	-	-	

12. Legal information

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Document status[1] [2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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